Exploring the Effect of Seed Layer Lattice Mismatch on the Crystallization Behavior of Metallic Glass NiTi Films

Sara Edmondson, Mechanical Engineering
Mentor: Jagannathan Rajagopalan, Mechanical and Aerospace Engineering, School for Engineering Of Matter, Transport, and Energy

Abstract

NiTi films are widely used as sensors, actuators, and switches in microelectromechanical systems (MEMS) because of their shape memory effect (SME). As-deposited NiTi films are amorphous and do not show SME. The high-temperature annealing required to crystallize NiTi films (to induce SME) leads to undesirable thermal stresses in MEMS. This project seeks to reduce the crystallization temperature (T_X) of amorphous NiTi films by incorporating carefully selected metallic seed layers. Different seed layers with low/high lattice mismatch will be explored to determine their effects on T_X. This approach, if successful, can help systematically control the T_X of NiTi films, leading to faster, energy-efficient MEMS fabrication and fewer post-fabrication failures.

Methods

Sample Preparation

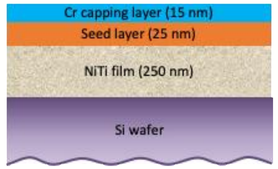
- Thin films deposited using AJA Orion 5 magnetron sputtering system.
- Step 1: Deposit ~250 nm thick NiTi film (51.5% Ni) on Si wafers by co-sputtering from Ni and Ti targets.
- Step 2: Deposit Cr, W, CrW and WNb seed layers (25 nm) on NiTi film without breaking vacuum. Seed layers have same crystal structure as NiTi to promote nucleation.
- Step 3: Cap the seed layer with an ~15 nm thick Cr layer to avoid oxidation of seed layer/NiTi film during annealing.

Crystallization Temperature Measurement:

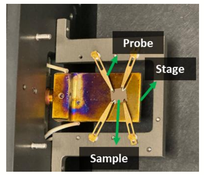
- Measure electrical resistivity of NiTi films with/without seed layers as a function of temperature (RT to 500°C).
- Resistivity measured using a 4-point probe in a Ecopia Hall effect measurement system.
- Crystallization is indicated by a steep drop in resistivity.

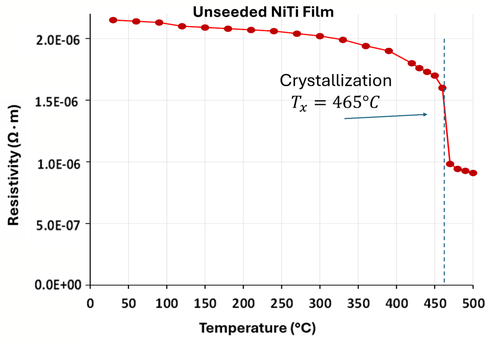
Experimental Setup and Results

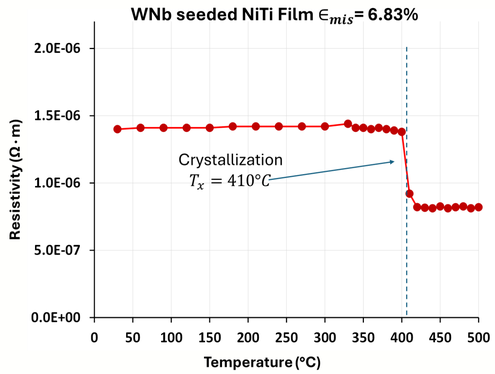
Sample cross-section

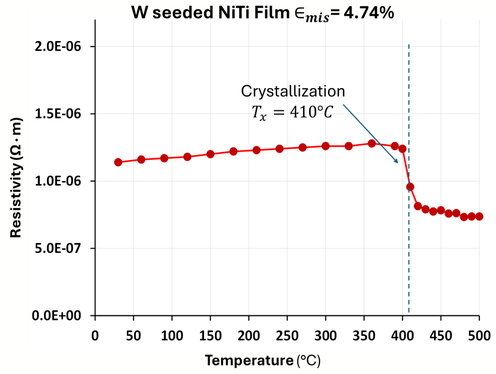


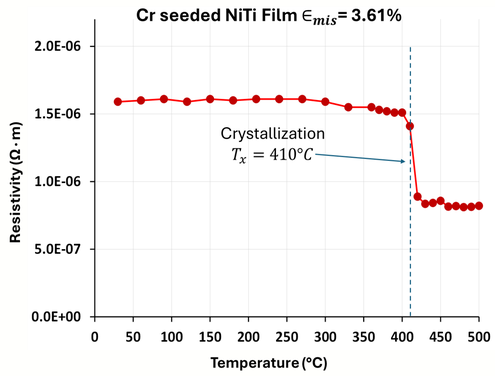
Electrical resistivity testing setup

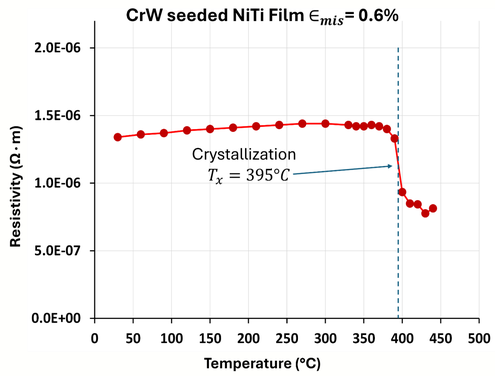












Conclusions

- Seed layers significantly reduce the crystallization temperature (T_X) of amorphous NiTi films.
- Reduction in T_X can be as high as 70°C for the case of CrW seed layers, which have the lowest lattice mismatch strain (ε_{mis} = 0.6%) with NiTi.
- Cr, W and WNb seeded NiTi films all have similar T_X even though their ε_{mis} are quite different. This suggests that chemical interactions between the seed layer and NiTi might also play a role in addition to lattice mismatch effects in determining T_X.
- Crystallization proceeds rapidly once it starts, which indicates that nucleation is the rate limiting step in the crystallization process.

Future Work

- Study chemical effects of the seed layers in addition to lattice mismatch on the crystallization kinetics of amorphous NiTi films.
- Measure the deposition induced stress in the seed layers and use it to obtain a more precise estimate of ε_{mis} of the seed layers.
- Examine the phase transformation behavior of NiTi films crystallized using seed layers.
- Explore if seed layers can be used to tune the phase transformation temperatures of NiTi films for different applications.

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Ira A. Fulton Schools of Engineering
Arizona State University